



# PBL56002D-Q

60 V, 1 A PNP/NPN loadswitch double transistor

26 October 2023

Product data sheet

## 1. General description

PNP low  $V_{CEsat}$  transistor and NPN Resistor-Equipped Transistor (RET) in a SOT457 (SC-74) small Surface Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Low  $V_{CEsat}$  transistor and resistor-equipped transistor in one package
- Low threshold voltage ( $< 1$  V) compared to MOSFET
- Low drive power required
- Space-saving solution
- Reduction of component count
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Supply line switches
- Battery charger switches
- High-side switches for LEDs, drivers and backlights
- Portable equipment

## 4. Quick reference data

Table 1. Quick reference data

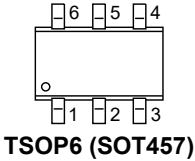
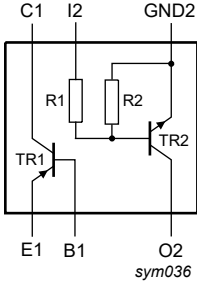
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>TR1; PNP low <math>V_{CEsat}</math> transistor</b>							
$V_{CEO}$	collector-emitter voltage	open base		-	-	-60	V
$I_C$	collector current		[1]	-	-	-1	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -1000$ mA; $I_B = -100$ mA; $T_{amb} = 25$ °C	[2]	-	255	340	m $\Omega$
<b>TR2; NPN resistor-equipped transistor</b>							
$V_{CEO}$	collector-emitter voltage	open base		-	-	50	V
$I_O$	output current			-	-	100	mA
R1	bias resistor 1 (input)			3.3	4.7	6.1	k $\Omega$
R2/R1	bias resistor ratio			0.8	1	1.2	

[1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[2] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	 <p>TSOP6 (SOT457)</p>	 <p>sym036</p>
2	B1	base TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	C1	collector TR1		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
<a href="#">PBL6002D-Q</a>	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	<a href="#">SOT457</a>

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBL6002D-Q	F2

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
<b>TR1; PNP low <math>V_{CEsat}</math> transistor</b>						
$V_{CBO}$	collector-base voltage	open emitter		-	-80	V
$V_{CEO}$	collector-emitter voltage	open base		-	-60	V
$V_{EBO}$	emitter-base voltage	open collector		-	-5	V
$I_C$	collector current		[1]	-	-700	mA
			[2]	-	-850	mA
			[3]	-	-1	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse		-	-2	A
$I_B$	base current			-	-300	mA
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms		-	-1000	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	250	mW
			[2]	-	350	mW
			[3]	-	400	mW

Symbol	Parameter	Conditions		Min	Max	Unit
<b>TR2; NPN resistor-equipped transistor</b>						
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	10	V
V <sub>I</sub>	input voltage			-10	30	V
I <sub>O</sub>	output current			-	100	mA
I <sub>CM</sub>	peak collector current			-	100	mA
P <sub>tot</sub>	total power dissipation		[1]	-	200	mW
			[2]	-	200	mW
			[3]	-	200	mW
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	400	mW
			[2]	-	530	mW
			[3]	-	600	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

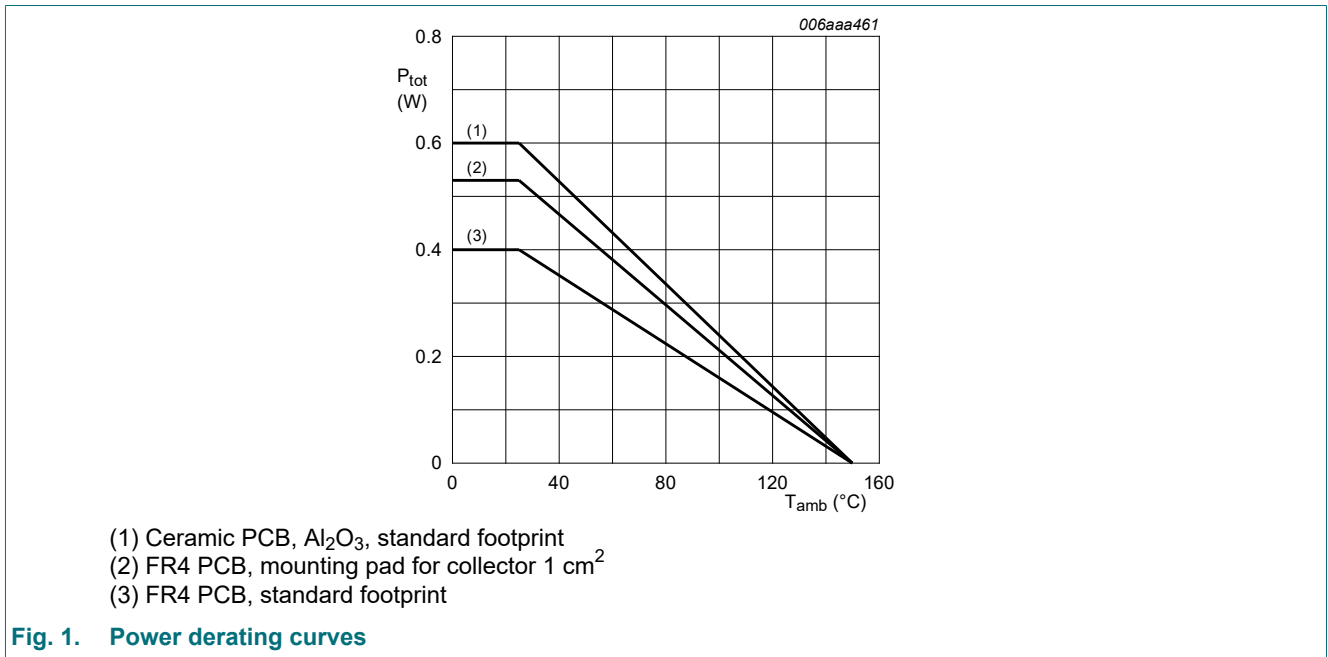


Fig. 1. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Per device</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	312	K/W
			[2]	-	-	236	K/W
			[3]	-	-	208	K/W
<b>TR1; PNP low <math>V_{CEsat}</math> transistor</b>							
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W	

- [1] Device mounted on an FR4 PCB, single-sided, copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

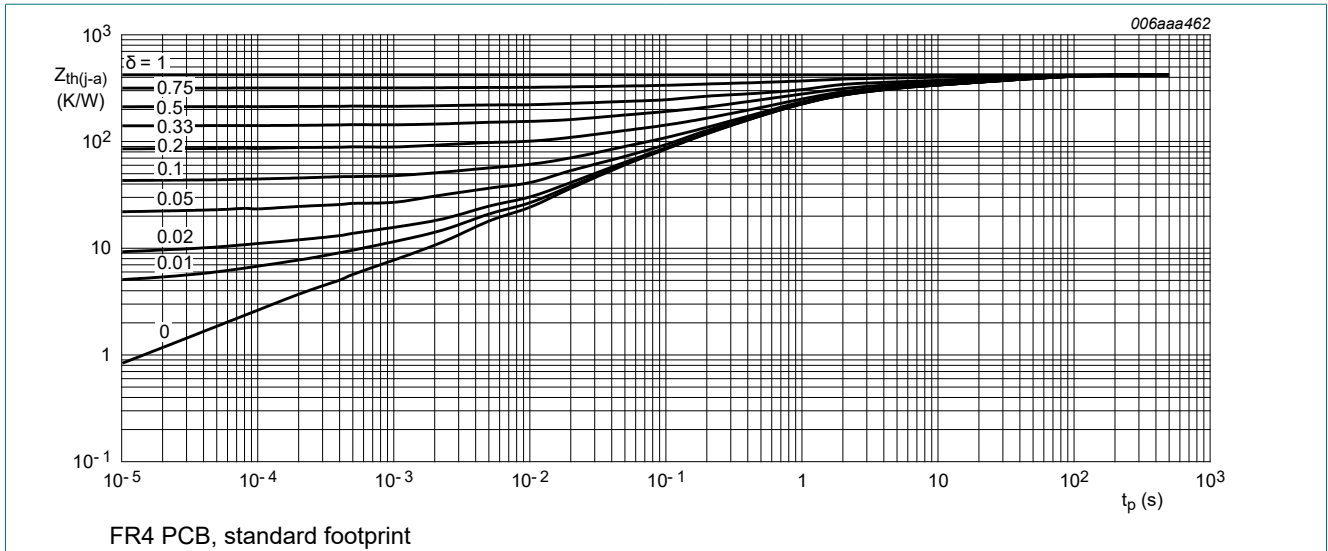


Fig. 2. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

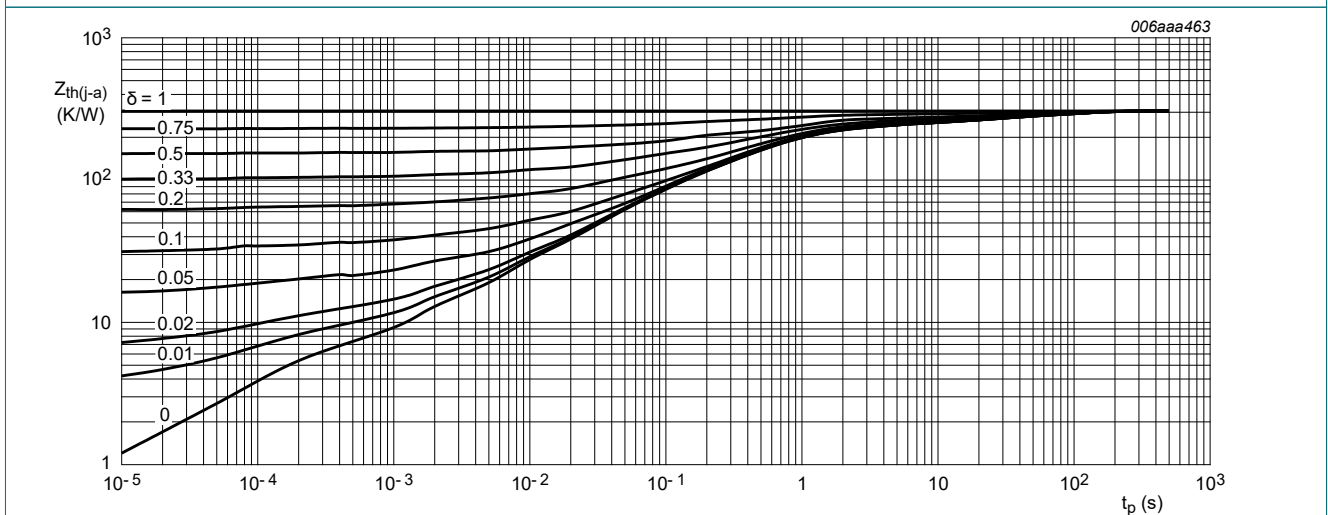
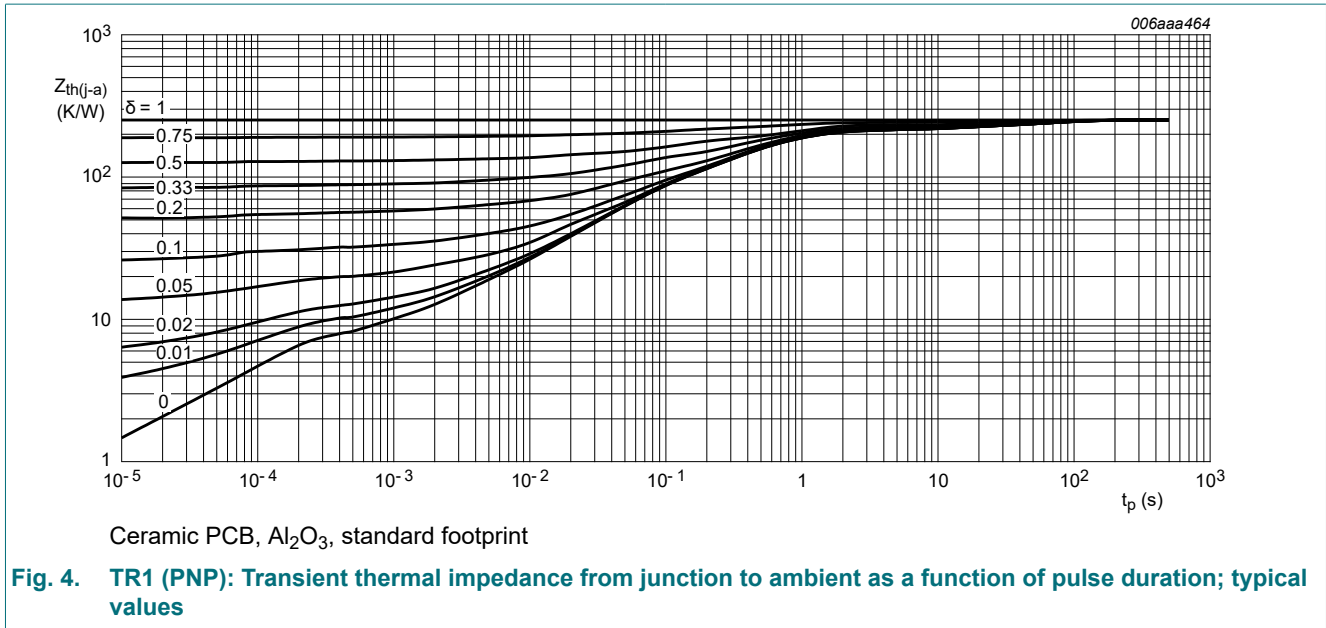


Fig. 3. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



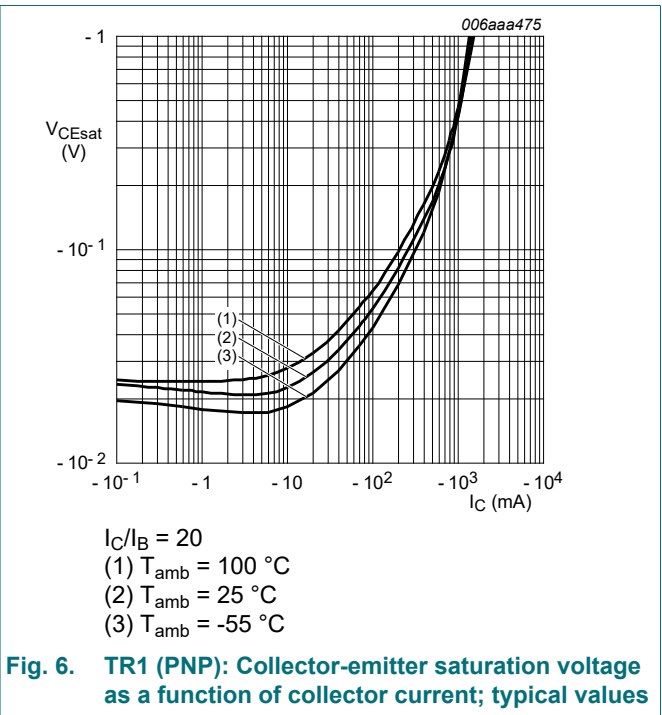
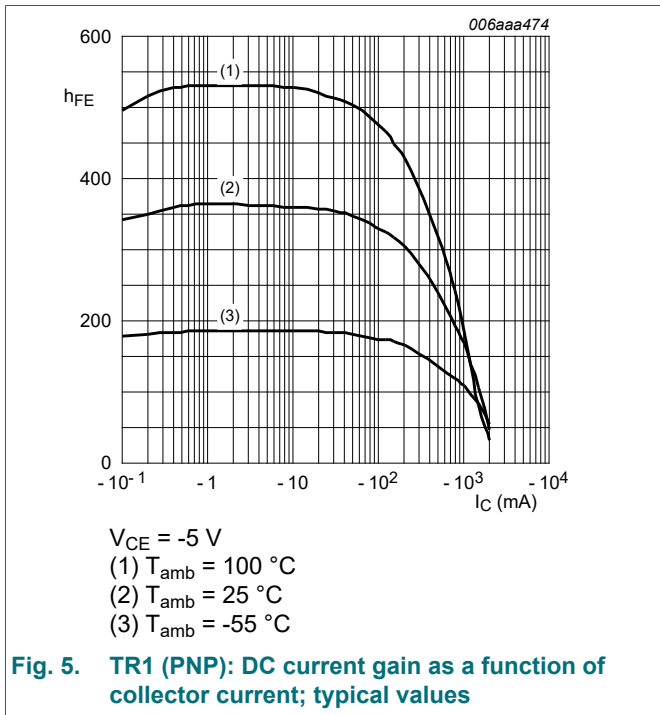
## 10. Characteristics

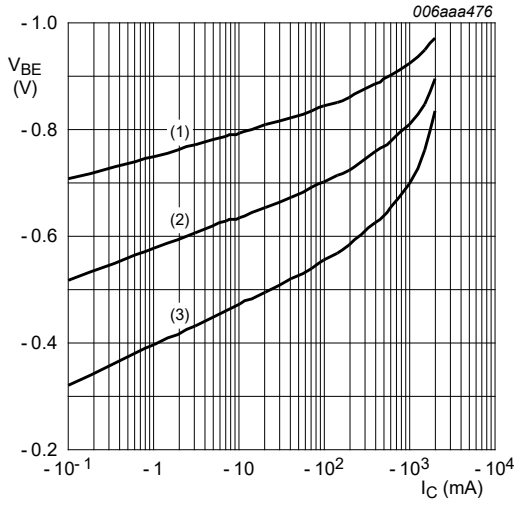
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR1; PNP low V<sub>CEsat</sub> transistor</b>						
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	µA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -60 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C	200	350	-	
		V <sub>CE</sub> = -5 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C [1]	150	230	-	
		V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1000 mA; T <sub>amb</sub> = 25 °C [1]	100	160	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -1 mA; T <sub>amb</sub> = 25 °C	-	-110	-175	mV
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C [1]	-	-135	-180	mV
		I <sub>C</sub> = -1000 mA; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C [1]	-	-255	-340	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	T <sub>amb</sub> = 25 °C [1]	-	255	340	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1000 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C [1]	-	-0.95	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1000 mA; T <sub>amb</sub> = 25 °C [1]	-	-0.82	-0.9	V
t <sub>d</sub>	delay time	I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA; I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	11	-	ns
t <sub>r</sub>	rise time		-	30	-	ns
t <sub>on</sub>	turn-on time		-	41	-	ns
t <sub>s</sub>	storage time		-	205	-	ns
t <sub>f</sub>	fall time		-	55	-	ns
t <sub>off</sub>	turn-off time		I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = 25 mA; I <sub>Boff</sub> = 25 A; T <sub>amb</sub> = 25 °C	-	260	-

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}$ ; $I_E = 0\text{ A}$ ; $i_e = 0\text{ A}$ ; $f = 1\text{ MHz}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	9	15	pF
$f_T$	transition frequency	$V_{CE} = -10\text{ V}$ ; $I_C = -50\text{ mA}$ ; $f = 100\text{ MHz}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	150	185	-	MHz
<b>TR2; NPN resistor-equipped transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}$ ; $I_E = 0\text{ A}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}$ ; $I_B = 0\text{ A}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{CE} = 30\text{ V}$ ; $I_B = 0\text{ A}$ ; $T_j = 150\text{ }^\circ\text{C}$	-	-	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}$ ; $I_C = 0\text{ A}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	900	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}$ ; $I_C = 20\text{ mA}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	30	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}$ ; $I_B = 0.5\text{ mA}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$ [1]	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}$ ; $I_C = 100\text{ }\mu\text{A}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	1.1	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}$ ; $I_C = 20\text{ mA}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	2.5	1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}$ ; $I_E = 0\text{ A}$ ; $i_e = 0\text{ A}$ ; $f = 1\text{ MHz}$ ; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	2.5	pF

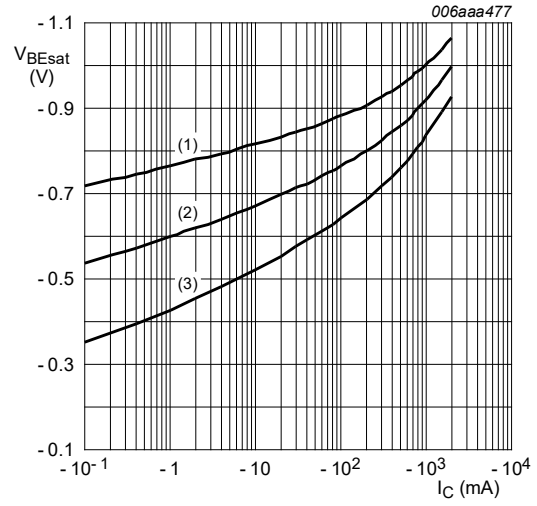
[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$





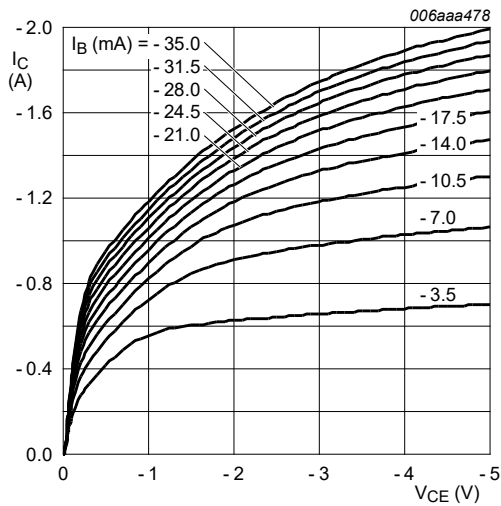
$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 7. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values**



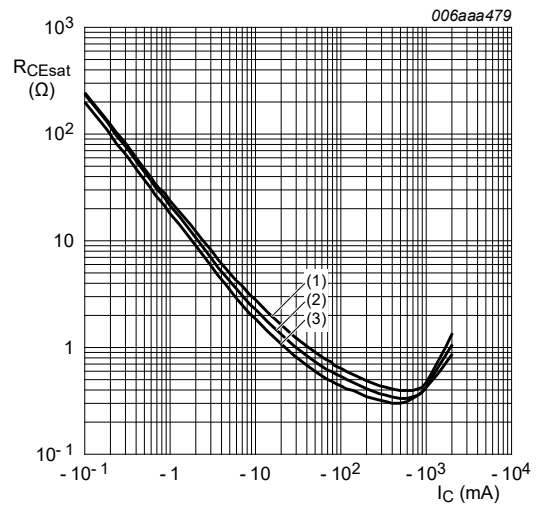
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 8. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values**



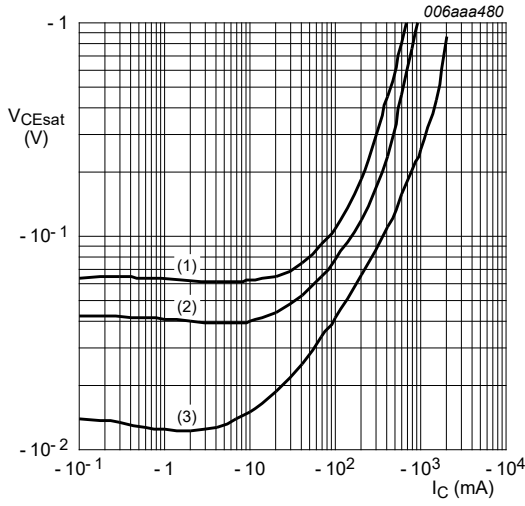
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 9. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values**



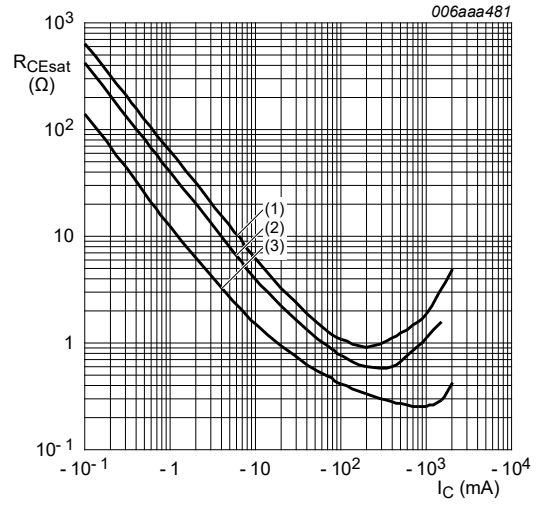
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 10. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values**



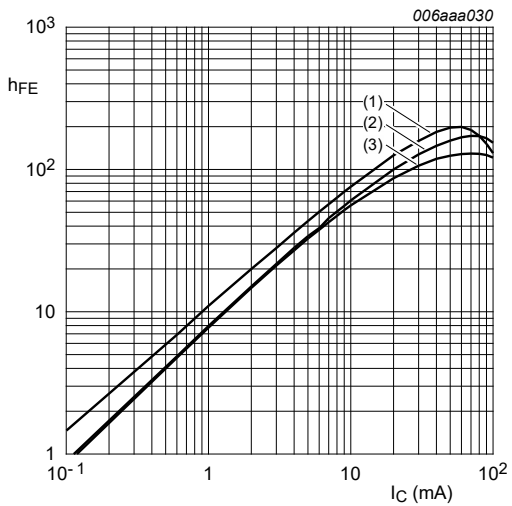
$T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig. 11. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values**



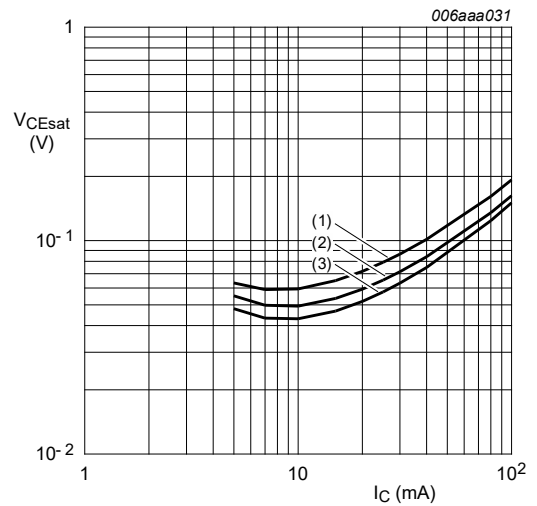
$T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig. 12. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values**



$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

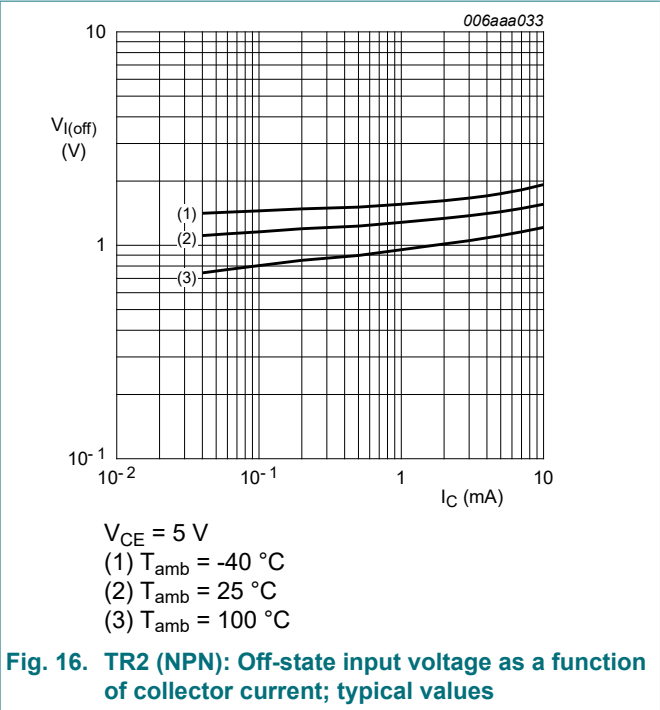
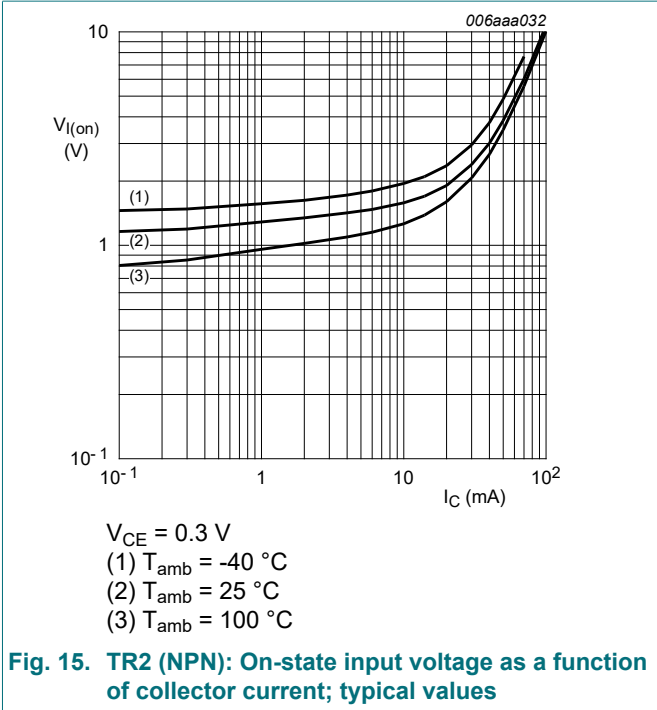
**Fig. 13. TR2 (NPN): DC current gain as a function of collector current; typical values**



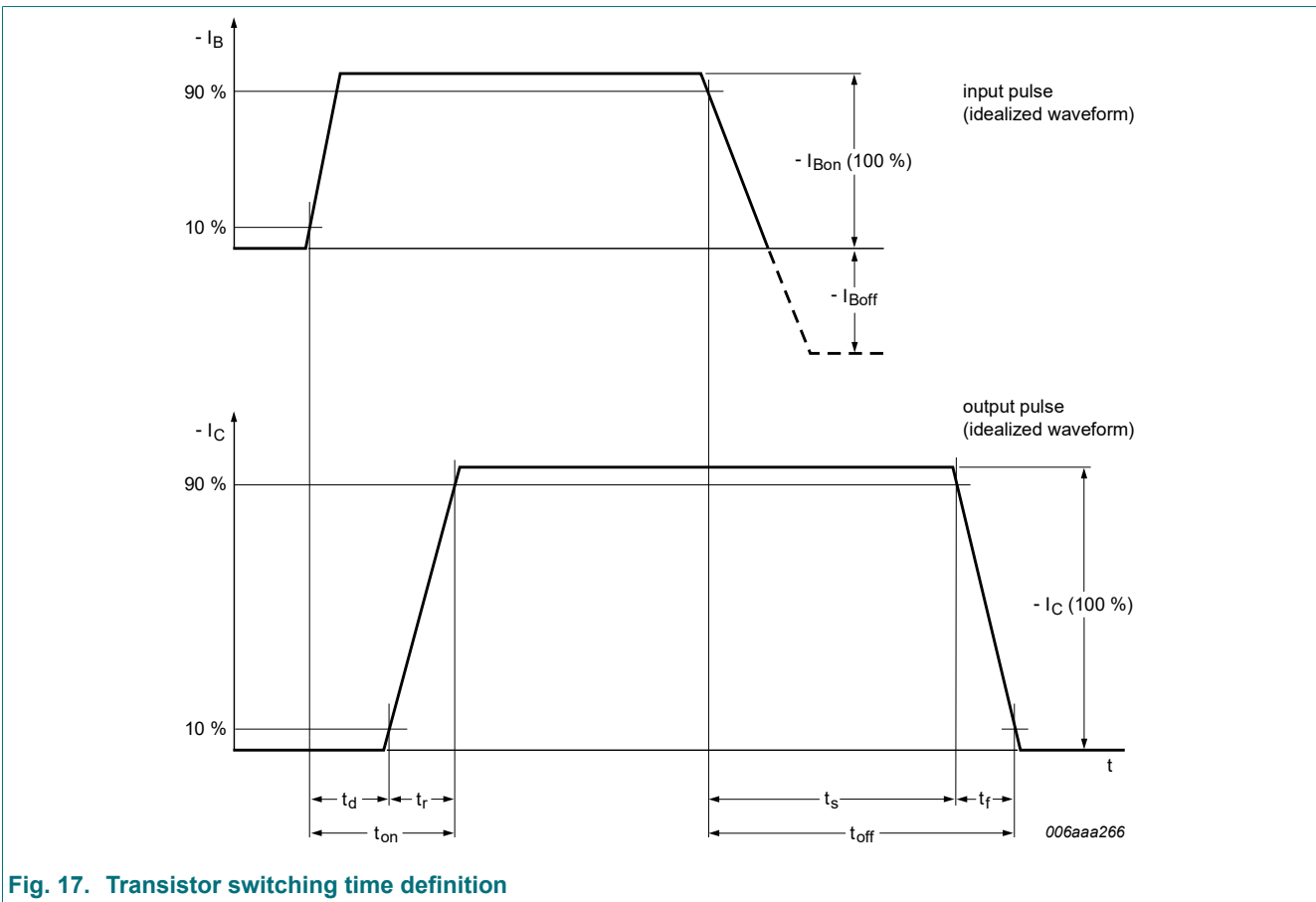
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

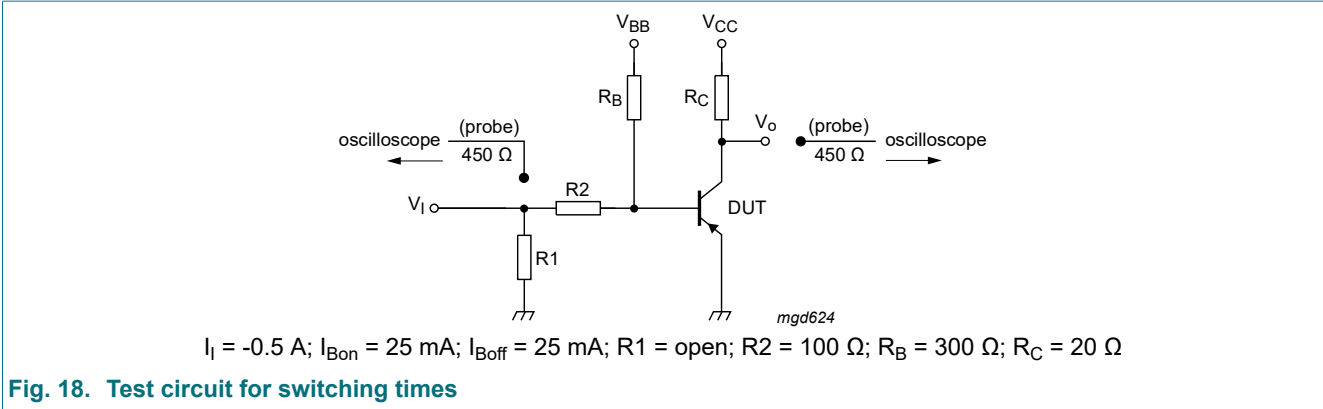
**Fig. 14. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values**





### 11. Test information

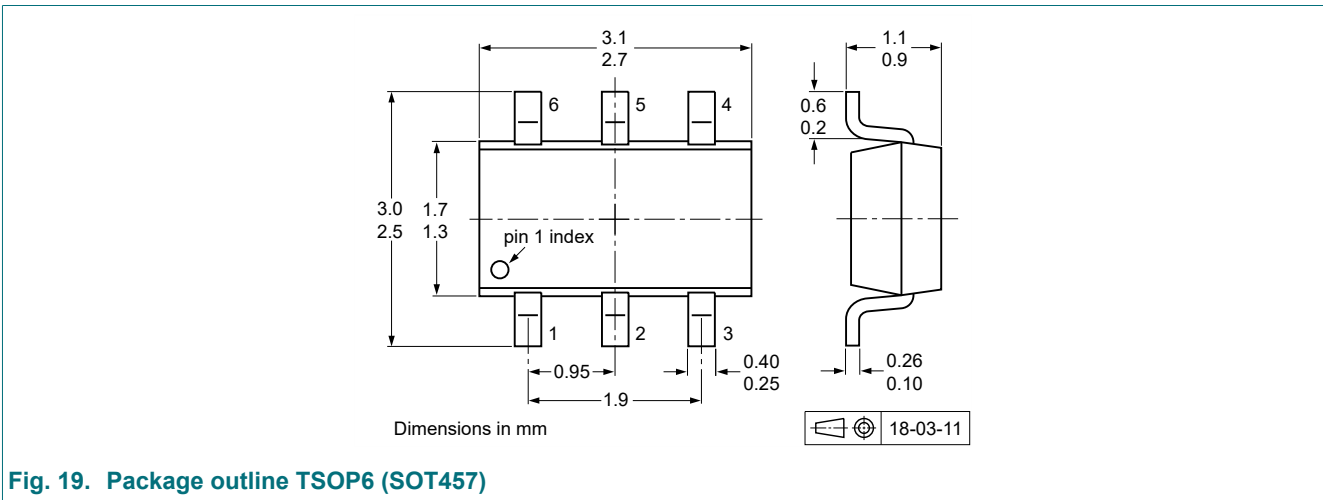




**Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**12. Package outline**



### 13. Soldering

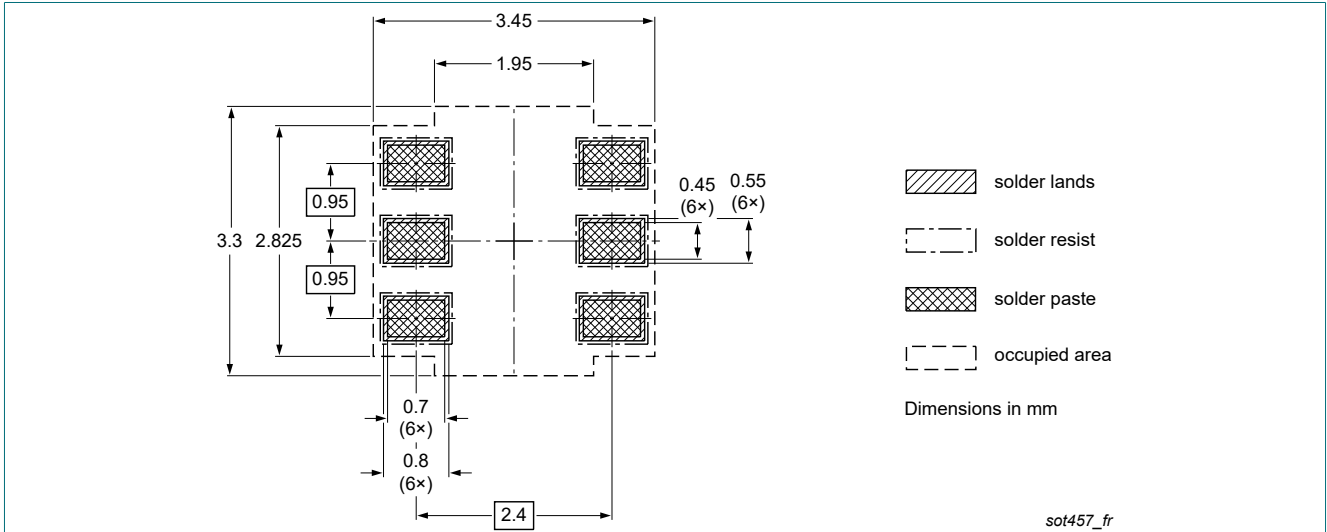


Fig. 20. Reflow soldering footprint for TSOP6 (SOT457)

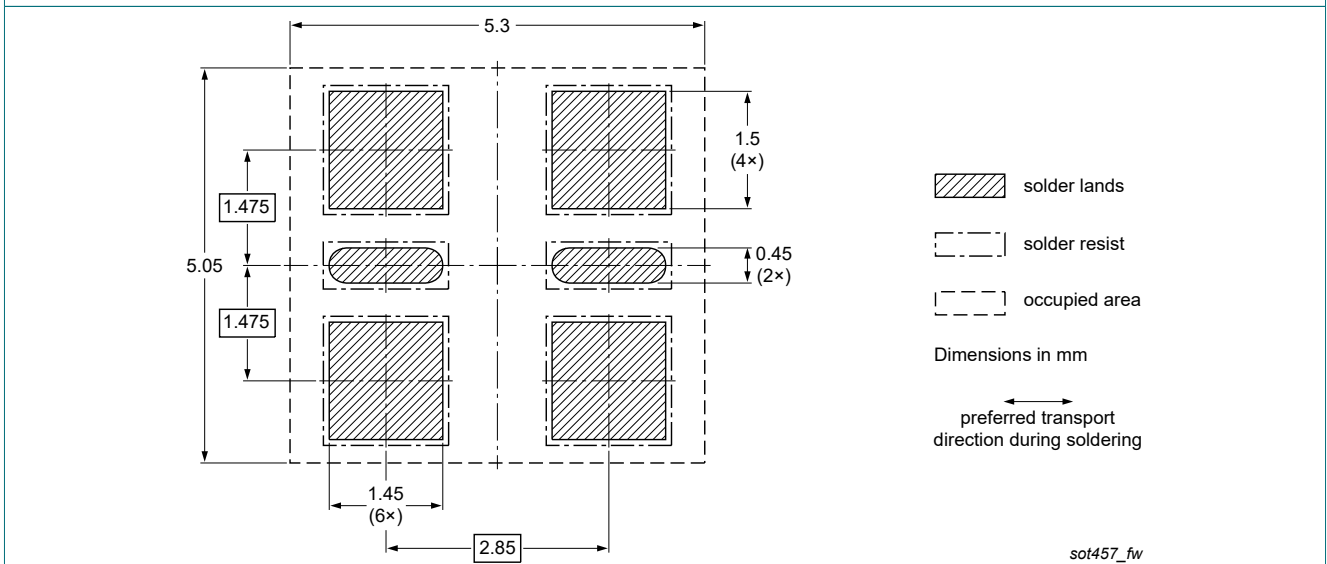


Fig. 21. Wave soldering footprint for TSOP6 (SOT457)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBLS6002D-Q v.1	20231026	Product data sheet	-	-

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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Date of release: 26 October 2023

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